



**THE DATASHEET OF
NRVB120ESFT1G**



Surface Mount Schottky Power Rectifier

Plastic SOD-123 Package

MBR120ESF, NRVB120ESF

This device uses the Schottky Barrier principle with a large area metal-to-silicon power diode. Ideally suited for low voltage, high frequency rectification or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system. This package also provides an easy to work with alternative to leadless 34 package style. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are AC-DC and DC-DC converters, reverse battery protection, and “Oring” of multiple supply voltages and any other application where performance and size are critical.

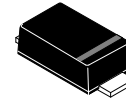
Features

- Guardring for Stress Protection
- Low Leakage
- 150°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Package Designed for Optimal Automated Board Assembly
- ESD Rating:
 - ◆ Human Body Model = 3B
 - ◆ Machine Model = C
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant*

Mechanical Characteristics

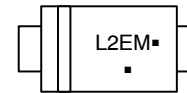
- Device Marking: L2E
- Polarity Designator: Cathode Band
- Weight: 11.7 mg (approximately)
- Case: Epoxy, Molded
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

SCHOTTKY BARRIER
 RECTIFIER
 1.0 AMPERES
 20 VOLTS



SOD-123FL
 CASE 498

MARKING DIAGRAM



L2E = Specific Device Code
 M = Date Code
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MBR120ESFT1G	SOD-123FL (Pb-Free)	3,000 / Tape & Reel **
NRVB120ESFT1G	SOD-123FL (Pb-Free)	3,000 / Tape & Reel **
MBR120ESFT3G	SOD-123FL (Pb-Free)	10,000 / Tape & Reel ***
NRVB120ESFT3G	SOD-123FL (Pb-Free)	10,000 / Tape & Reel ***

** 8 mm Tape, 7" Reel

*** 8 mm Tape, 13" Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR120ESF, NRVB120ESF

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	V
Average Rectified Forward Current (At Rated V_R , $T_L = 140^\circ\text{C}$)	I_O	1.0	A
Peak Repetitive Forward Current (At Rated V_R , Square Wave, 20 kHz, $T_L = 125^\circ\text{C}$)	I_{FRM}	2.0	A
Non-Repetitive Peak Surge Current (Non-Repetitive peak surge current, halfwave, single phase, 60 Hz)	I_{FSM}	40	A
Storage Temperature	T_{stg}	-65 to 150	$^\circ\text{C}$
Operating Junction Temperature	T_J	-65 to 150	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R , $T_J = 25^\circ\text{C}$)	dv/dt	10,000	V/ μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance – Junction-to-Lead (Note 1)	R_{tjl}	26	$^\circ\text{C}/\text{W}$
Thermal Resistance – Junction-to-Lead (Note 2)	R_{tjl}	21	
Thermal Resistance – Junction-to-Ambient (Note 1)	R_{tja}	325	
Thermal Resistance – Junction-to-Ambient (Note 2)	R_{tja}	82	

1. Mounted with minimum recommended pad size, PC Board FR4.
2. Mounted with 1 in. copper pad (Cu area 700 mm²).

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value		Unit
Maximum Instantaneous Forward Voltage (Note 3), See Figure 2	V_F	$T_J = 25^\circ\text{C}$	$T_J = 100^\circ\text{C}$	V
($I_F = 0.1\text{ A}$)		0.455	0.360	
($I_F = 1.0\text{ A}$) ($I_F = 2.0\text{ A}$)		0.530 0.595	0.455 0.540	
Maximum Instantaneous Reverse Current (Note 3), See Figure 4	I_R	$T_J = 25^\circ\text{C}$	$T_J = 100^\circ\text{C}$	μA
($V_R = 20\text{ V}$)		10	1600	
($V_R = 10\text{ V}$) ($V_R = 5.0\text{ V}$)		1.0 0.5	500 300	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width $\leq 250\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

MBR120ESF, NRVB120ESF

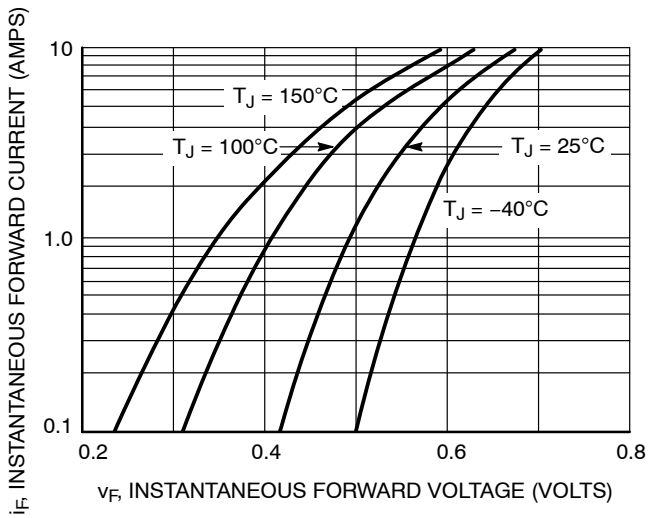


Figure 1. Typical Forward Voltage

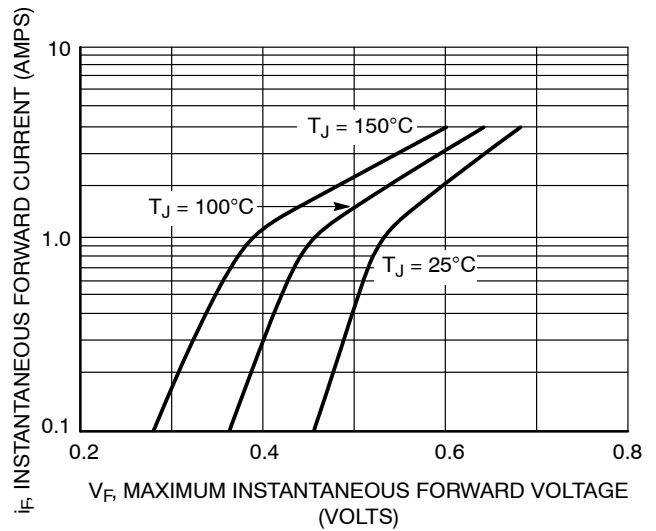


Figure 2. Maximum Forward Voltage

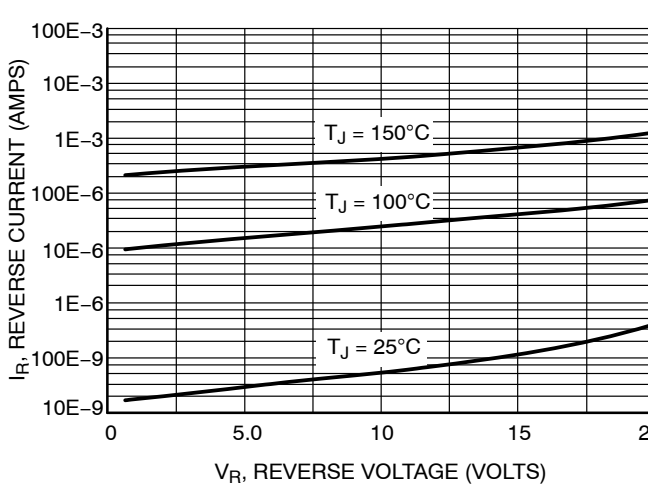


Figure 3. Typical Reverse Current

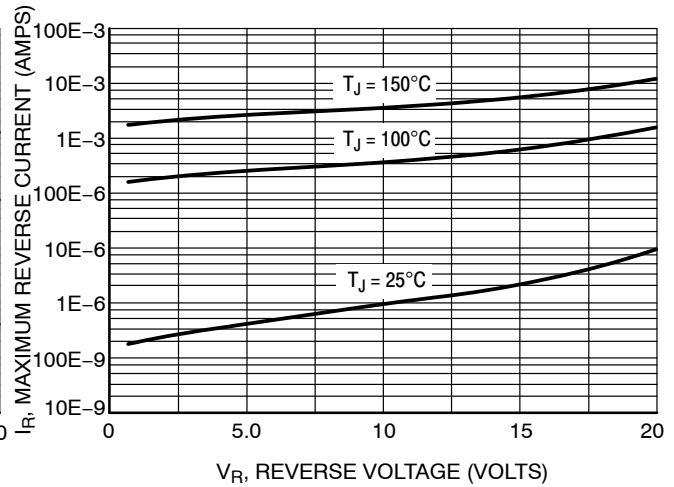


Figure 4. Maximum Reverse Current

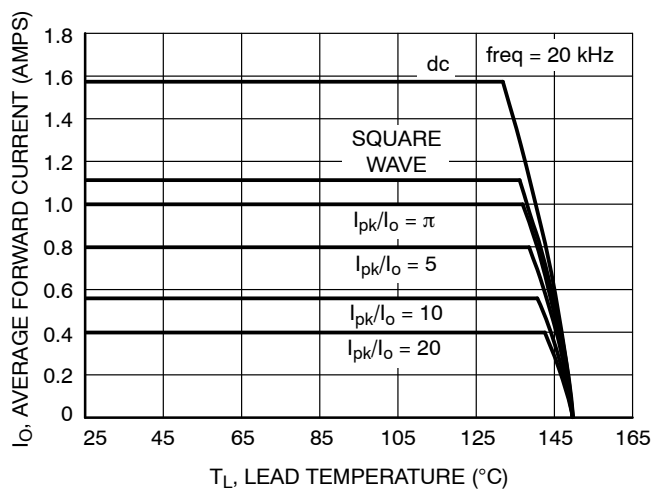


Figure 5. Current Derating

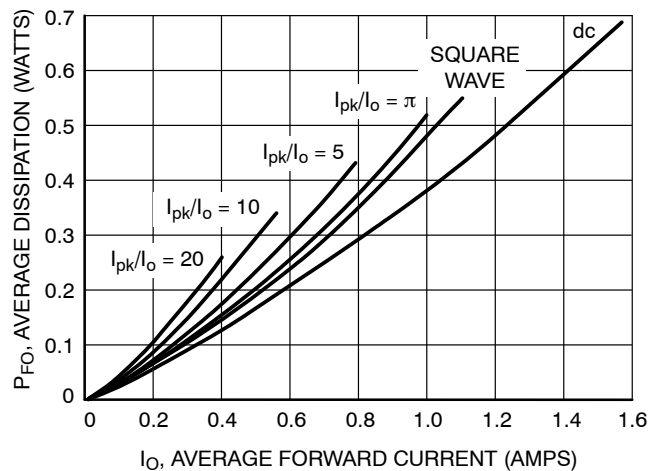


Figure 6. Forward Power Dissipation

MBR120ESF, NRVB120ESF

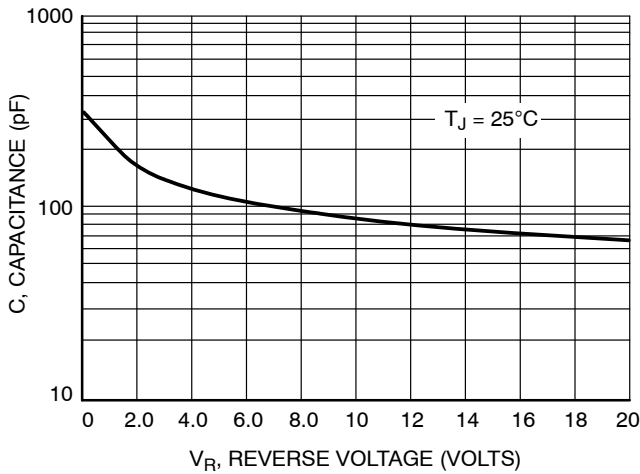


Figure 7. Capacitance

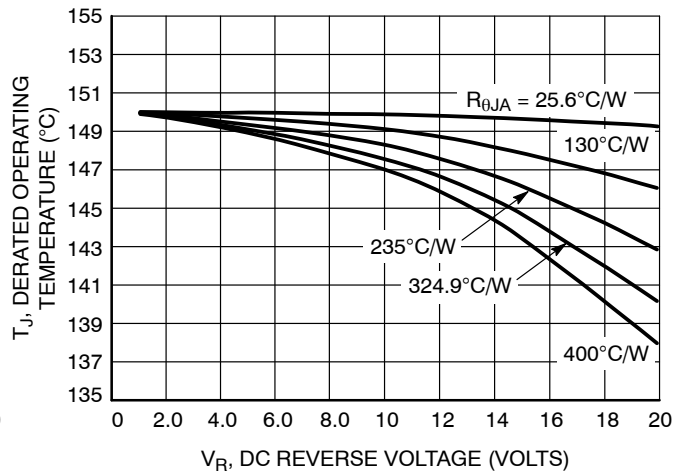


Figure 8. Typical Operating Temperature Derating*

* Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_J may be calculated from the equation:

$$T_J = T_{Jmax} - r(t)(P_f + P_r) \text{ where}$$

$r(t)$ = thermal impedance under given conditions,
 P_f = forward power dissipation, and
 P_r = reverse power dissipation

This graph displays the derated allowable T_J due to reverse bias under DC conditions only and is calculated as $T_J = T_{Jmax} - r(t)P_r$, where $r(t) = R_{thja}$. For other power applications further calculations must be performed.

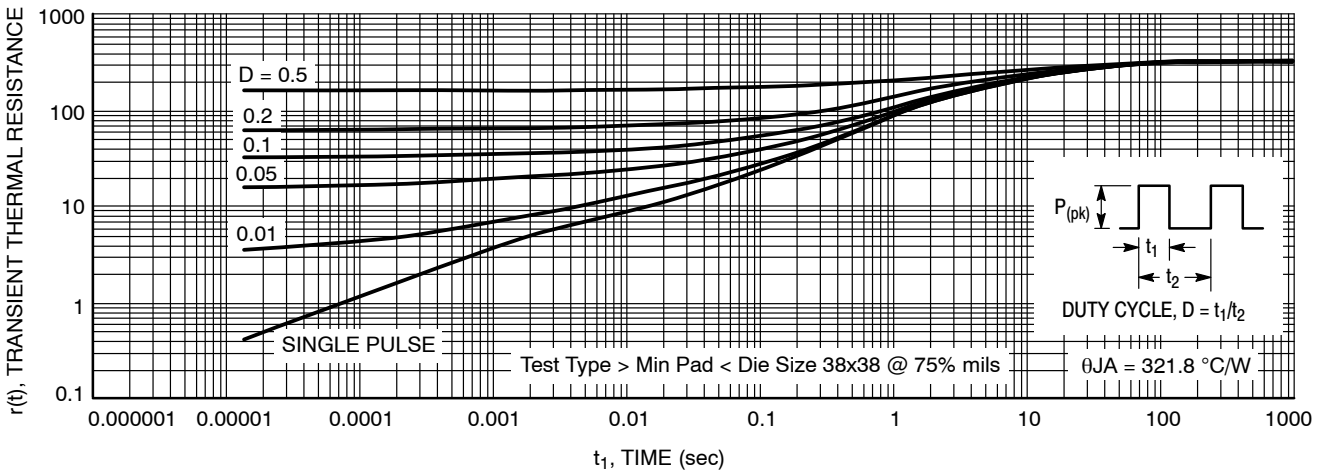


Figure 9. Thermal Response

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



SOD-123-2 1.65x2.70x0.90
CASE 498
ISSUE E

DATE 22 AUG 2023



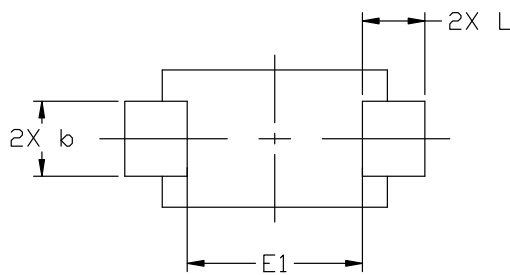
TOP VIEW



END VIEW

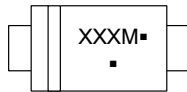


SIDE VIEW



BOTTOM VIEW

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
 M = Date Code
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN.	NDM.	MAX.
A	0.90	0.95	0.98
A1	0.00	0.05	0.10
A2	0.85	0.90	0.95
b	0.70	0.90	1.10
c	0.10	0.15	0.20
D	1.50	1.65	1.80
E	2.50	2.70	2.90
E1	1.70	2.10	2.50
H _E	3.40	3.60	3.80
L	0.55	0.75	0.95
θ	0°	---	8°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS b AND L ARE TO BE MEASURED ON A FLAT SECTION OF THE LEAD BETWEEN 0.10 AND 0.25 FROM THE LEAD TIP.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH PROTRUSIONS, OR GATE BURRS.
5. FLAT LEAD.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the IN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON11184D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOD-123-2 1.65x2.70x0.90	PAGE 1 OF 1

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

- ⊖ [View NRVB120ESFT1G on WIN SOURCE](#)
- ⊖ [ON Semiconductor Information](#)

Optimize Your Supply Chain with WIN SOURCE Solutions

- ✓ Global Sourcing Solution
- ✓ Obsolete Management
- ✓ Cost Control Management
- ✓ Shortage Management
- ✓ Alternative Solution
- ✓ Excess Inventory Management